Product data sheet

1. General description

Hyperfast epitaxial rectifier diode in a SOD113 (2-lead TO-220F) plastic package specifically for use in CCM PFC applications for reduced switching losses.

2. Features and benefits

- · Allows use of smaller MOSFETs and heatsinks
- Isolated package
- · Low thermal resistance
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET
- Superfast switching

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Desk top computer power supplies
- Flat panel TV power supplies
- Power supply adapters
- · Server power supplies
- · Telecom power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			6	000		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; $T_h \le 93$ °C; Fig. 1; Fig. 2			8		А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; square-wave pulse	16			А	
I _{FSM} non-repetitive pea forward current	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	110		Α		
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	120			Α	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>		-	2.35	3.2	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	2	2.4	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 6		-	12.5	-	ns
		$I_F = 8 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 125 \text{ °C}$; Fig. 6; Fig. 7		-	21	-	ns
Q _r	recovered charge	$I_F = 8 \text{ A}; \ V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ Tj = 125 °C; Fig. 5; Fig. 6		-	40	-	nC

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		K - ↓ A
mb	n.c.	mounting base; isolated		001aaa020
			U U 1 2	
			SOD113 (2-lead TO-220F)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYC58X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113		

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC58X-600	BYC58X-600

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 93$ °C; Fig. 1; Fig. 2;	8	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; square-wave pulse	16	Α
I _{FSM}	non-repetitive peak	$t_p = 10 \text{ ms; } T_{j(init)} = 25 \text{ °C; sine-wave pulse}$	110	Α
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	120	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

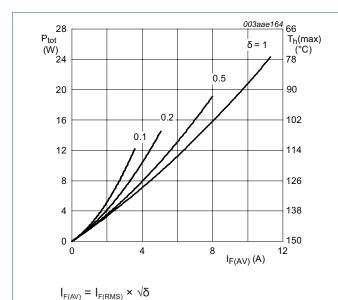
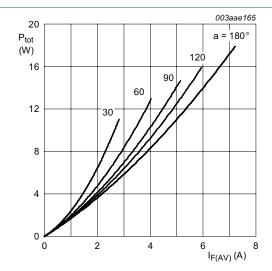


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

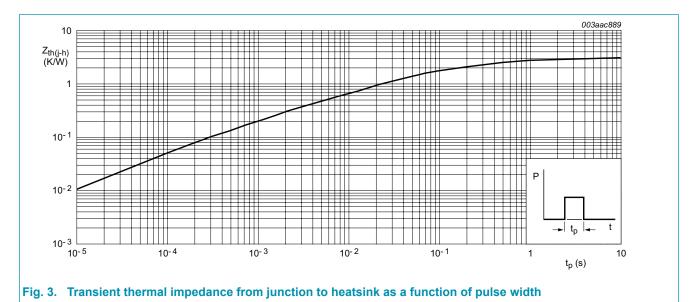
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig 3	-	2.5	3	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



10. Isolation characteristics

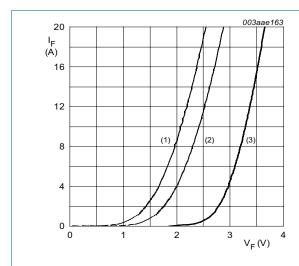
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

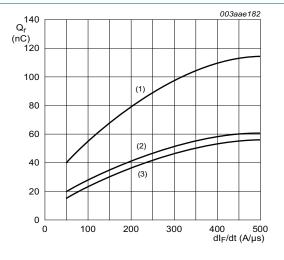
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>	-	2.35	3.2	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	2	2.4	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	150	μA
Dynamic	characteristics					'
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$	-	12.5	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 6; Fig. 7$	-	21	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 ^{\circ}\text{C}$	-	4	5.5	А
Q _r	recovered charge	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 5; Fig. 6$	-	40	-	nC



(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 4. Forward current as a function of forward voltage

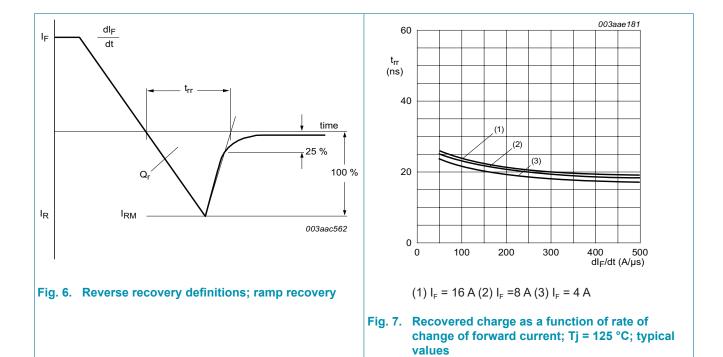


(1) $I_F = 16 A (2) I_F = 8 A (3) I_F = 4 A$

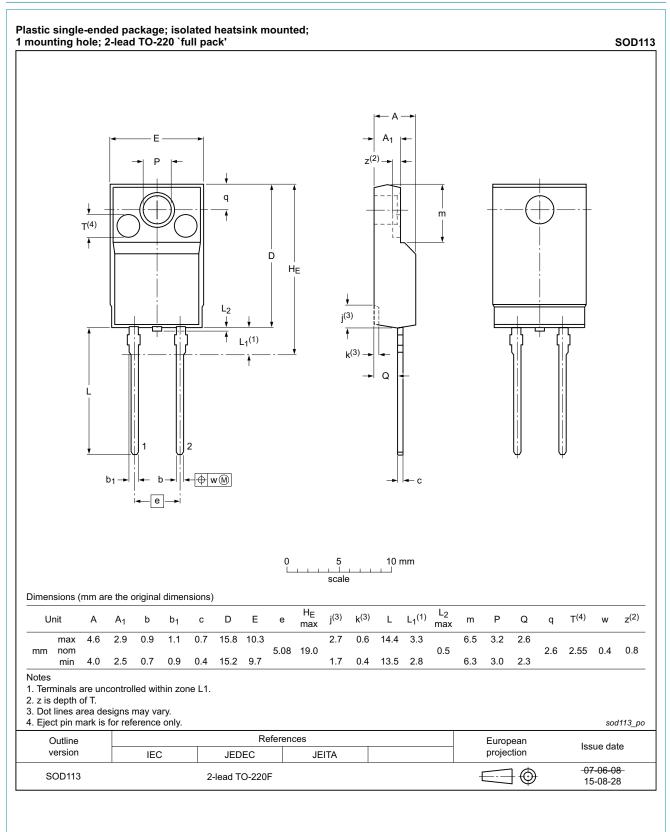
Fig. 5. Recovered charge as a function of rate of change of forward current; Tj = 125 °C; typical values

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12. Package outline



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13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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